The VA1'

Specifications v0.92
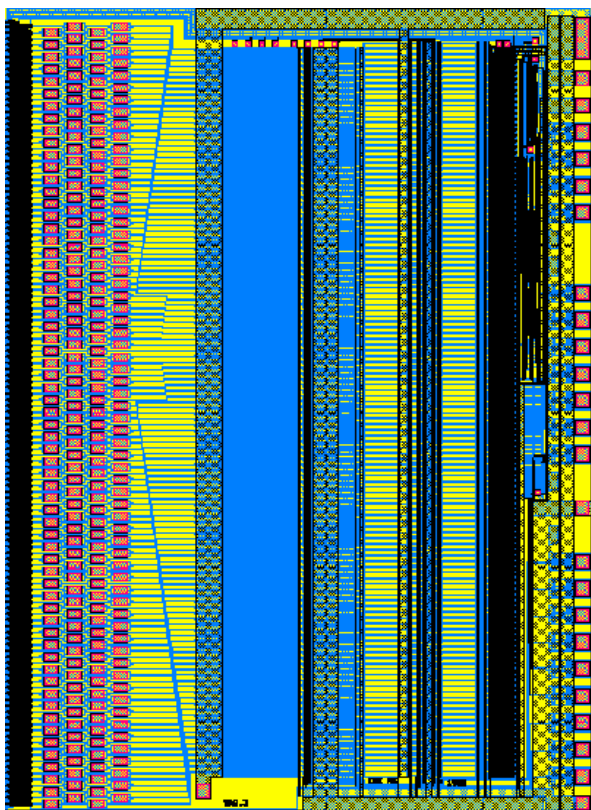
The Table of Contents

1 General

- Description:

    The VA1' ASIC is a 128 channel low-noise/low power charge sensitive preamplifier-shaper circuit, with simultaneous sample and hold, multiplexed analogue readout and calibration facilities. The part is a pin compatible replacement for VA1.

- Application Areas:

    Silicon strip, or other semiconductor, detectors of higher capacitance (20-100 pF)

- Vendor:

    Ideas ASA
    Veritasveien 9, 1322 Høvik, Norway.

    Phone: +47-67 81 65 00
    Fax: +47-67 81 65 01
    e-mail: Sales@ideas.no, http:/www.ideas.no/

- Availability:

    Available as unpackaged, wafer tested dices or mounted on hybrids (dedicated or standard designs). Normal stock goods.

2 Physical

- Process: 0.8 µm N-well CMOS, double-poly, double metal.
- Die size: 6.12 mm x 4.04 mm, thickness: ~ 600 µm

Recommended chip pitch when several chips are mounted in cascade on a hybrid: 6.4 mm or more. That is; fits well with true 50 µm pitch strip sensors.

- Input bonding pads:

Four rows. Normal connection to rows 1 and 2, redundant pads in rows 3 and 4.

Pad size: 50 µm x 90 µm
Pad pitch: 91.2 µm
Row pitch: 170 µm   (see. fig. 2&3)

- Output, control and power pads:

Single row.

    Pad size: 90 µm x 90 µm
    Pad pitch: 200 µm   (see fig. 2)

- Radiation hardness:

    1 Mrad

3 Electrical

Power rails: Vdd = +2.0V, Vss = -2.0V

                          Each with separate connections for analogue (avdd and avss)
                          and digital sections (dvdd, dvss) of the chip.

Back contact: metalized, connect to avss (-2 V)

Current draw: Quiescent (typical values):

                          dvdd: < 10   µA
                          dvss: < 10   µA
                          avdd: 11.5 mA
                          avss: - 73   mA
                          gnd: 61.5 mA

Input bias currents: Nominal values   Minimal values[1]
                          (all driven to devices (e.g. resistors) referred to avdd)

                          pre_bias: 500 µA   pre_bias: 50 µA
                          sha_bias: 22 µA   sha_bias: 5 µA
                          ibuf: 140 µA   ibuf: 40 µA
                          (ibuf only during readout)
Peaking time: Nominal: 1µs
                          Adjustable: 1µs - 3µs

Power dissipation: Typical values
                          Quiescent: 170 mW (1.3mW/ch)   Minimal: 68 mW
                          Peak   177 mW

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[1] at this conditions performance may vary from nominal specs

ESD Protection:	Inputs:	None

Analogue out p & m :   None
Controls (include. shift out b):
~ 300Ω series resistor and protection diodes to Vdd and Vss.

Input stage: Input device: PMOS referenced to gnd

Signal input potential:~ -1.2 V to -1.3 V

Gain: ~ 12.5 mV/fC nominal with differential outputs each driving
500 Ω. Current gain is about 10 µA/fC. The gain depends on
setting parameters like VFS, Sha_bias etc.

Linear range: ± 35fC (approx ± 10 MIP in 300um Si) (can handle both signal polarities)
70fC in single polarity can be used with adjustment of VREF.

Noise (ENC):   Typical values:

180 + 7.5/pF e$^-$rms for 1 µsec peaking time
165 + 6.1/pF e$^-$rms for 2 µsec peaking time

Readout: Controlled via 128-bit (output) shift register.

Analogue outputs (outp, outm) of two or more chips can be
connected in parallel to drive the inputs of an external,
differential, transimpedance amplifier.
Max. read-out is 10 MHz, here care has to be taken not to load
the output buffer with to high capacitance and resistance.

Calibration/test: Voltage step applied via external 1.8 pF capacitor to the cal-
input. 2 mV step represents 3.6fC.
(1 MIP in 300um Si = 22400 e$^-$ or 3.6 fC).
Some additional noise has to be taken into account in test
mode due to serial resistance and additional capacitance.
Calibration signal can be given to one channel in a given chip
at a time. The channel is selected via a 128-bit (input) shift
register.

4 Pad Description

The output, control and power pads are listed below from top to bottom. (see chip plot on next page (Fig. 1.)

Pad name	Type	Description	Nominal value
gnd	p	signal ground	0 V
dvdd	p	digital vdd	+2.0 V
dvss	p	digital vss	-2.0 V
delay_adjust	ai	not in use	connect to gnd
delay_on	di	not in use	connect to dvss
holdb	di	used to hold analogue data, see fig. 3.	Logical
dummy (hold)	di	*)	Logical
dreset	di	reset of digital part	Logical
dummy (dresetb)	di	*)	Logical
shift_in_b	di	start pulse for read-out	Logical
dummy (ck)	di	*)	Logical
ckb	di	clock for read-out register, see fig. 3.	Logical
shift_out_b	do	Signalling end of read-out. Can be used as shift_in_b for next chip.	Logical
test_on	di	Turns chip into test-mode	Logical
avss	p	Analogue vss (+ chip backplane)	-2.0 V
pre_bias	ai	Bias current for pre-amplifiers.	500 μA
sha_bias	ai	Bias current for shaper-amplifiers.	22 μA
vref	ai	not in use. (recommended connected to decoupling capacitor).	
ibuf	ai	Bias-current for output-buffer.	140 μA
outm	ao	Negative output signal (current)	
outp	ao	Positive output signal (current)	
vfs	ai	Control voltage to feedback resistance in shaper-amplifier	700 mV
vfp	ai	Control voltage to feedback resistance in pre-amplifier	-0.2 V[2]
cal	ai	Test input signal	1 MIP
avdd	p	Analogue vdd	+2.0 V

p = power, di = digital in, do = digital out, ai = analogue in, ao = analogue out

*) These 'dummy' signals are recommended for high performance. They should be used to add complementary signals to the effective ones in order to minimise digital signal-feedthrough to the analogue output.

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[2] see chapter 'Useful Hints'
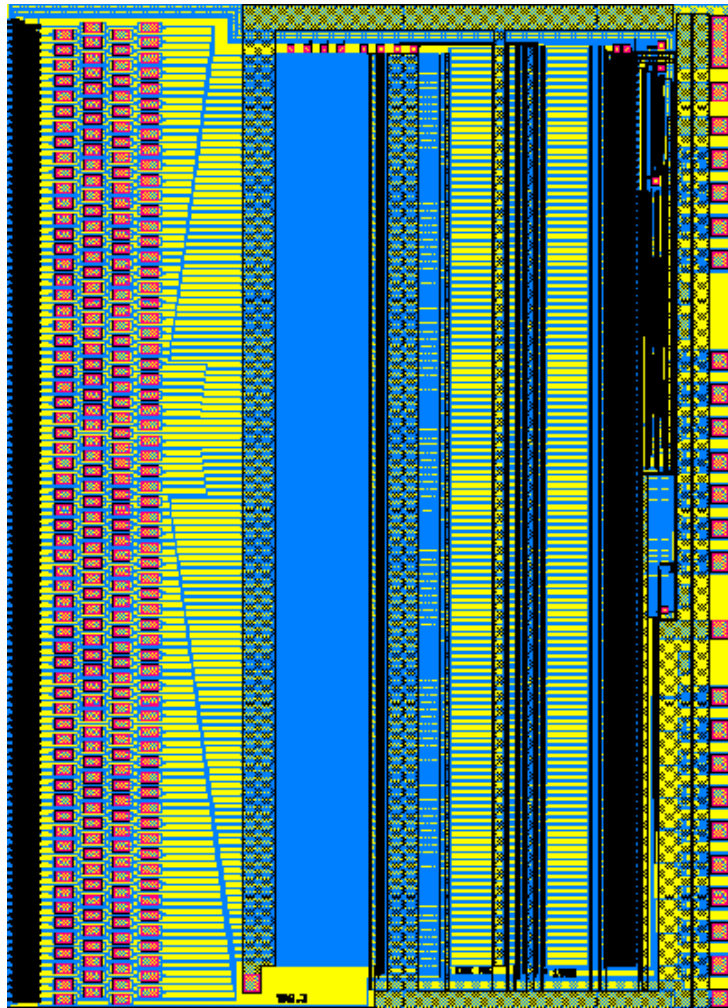
gnd

dvdd

dvss

delay_adjust
delay_on

holdb

hold (dummy)

dreset

dresetb (dummy)
shift in b

ck (dummy)

ckb

shift out b

test on

avss

pre_bias

sha_bias
vref

ibuf

outm

outp
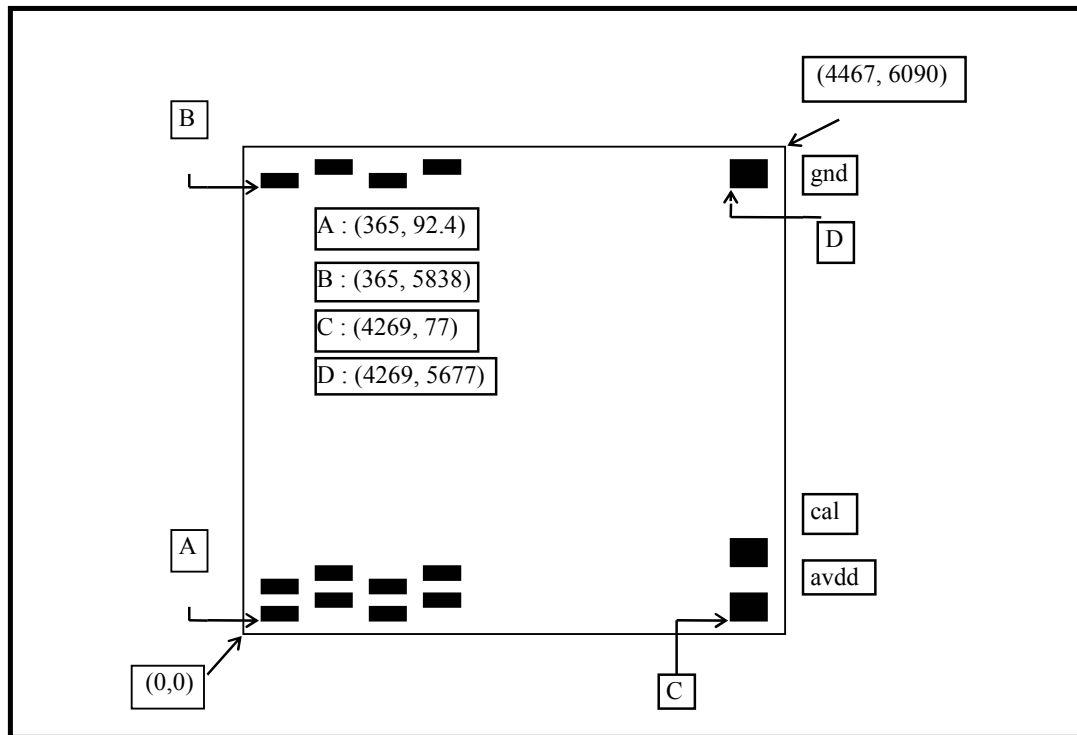
vfs

vfp

cal

avdd

The VA1' circuit.

Fig. 2 Chip geometry & pad placement (Not to scale - all dimensions in μm. Please note that the referred co-ordinates are layout co-ordinates. Add 50-100 μm on each side for scribe/cutting tolerances).
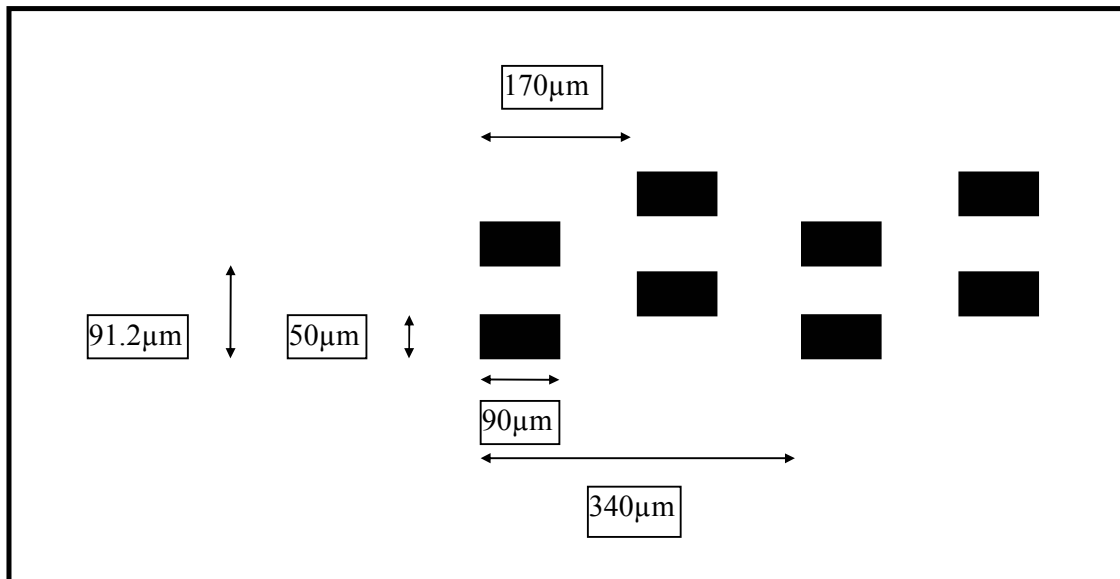

Fig. 3. Definition of input pad size and pitch.

5 Functional Description

As shown in Fig. 4 the chip consists of 128 identical parallel charge sensitive amplifiers. The output of all amplifiers enters corresponding inputs of a 128 channel multiplexer. The switches in the multiplexer are controlled by a bit-register which runs in parallel. The output of the mux. goes directly out of the chip via the output buffer (signal = 'outp' - 'outm'). Only one of the switches in the mux can be ¨on¨ at a time. That is one amplifier (channel) at a time can be seen on the output of the chip. The bit in the register ripples in sequence from the top- to the bottom- channel by clocking 'ckb'. The clock can be stopped at any point which will leave the connection between the current channel and the output, which remains enabled.
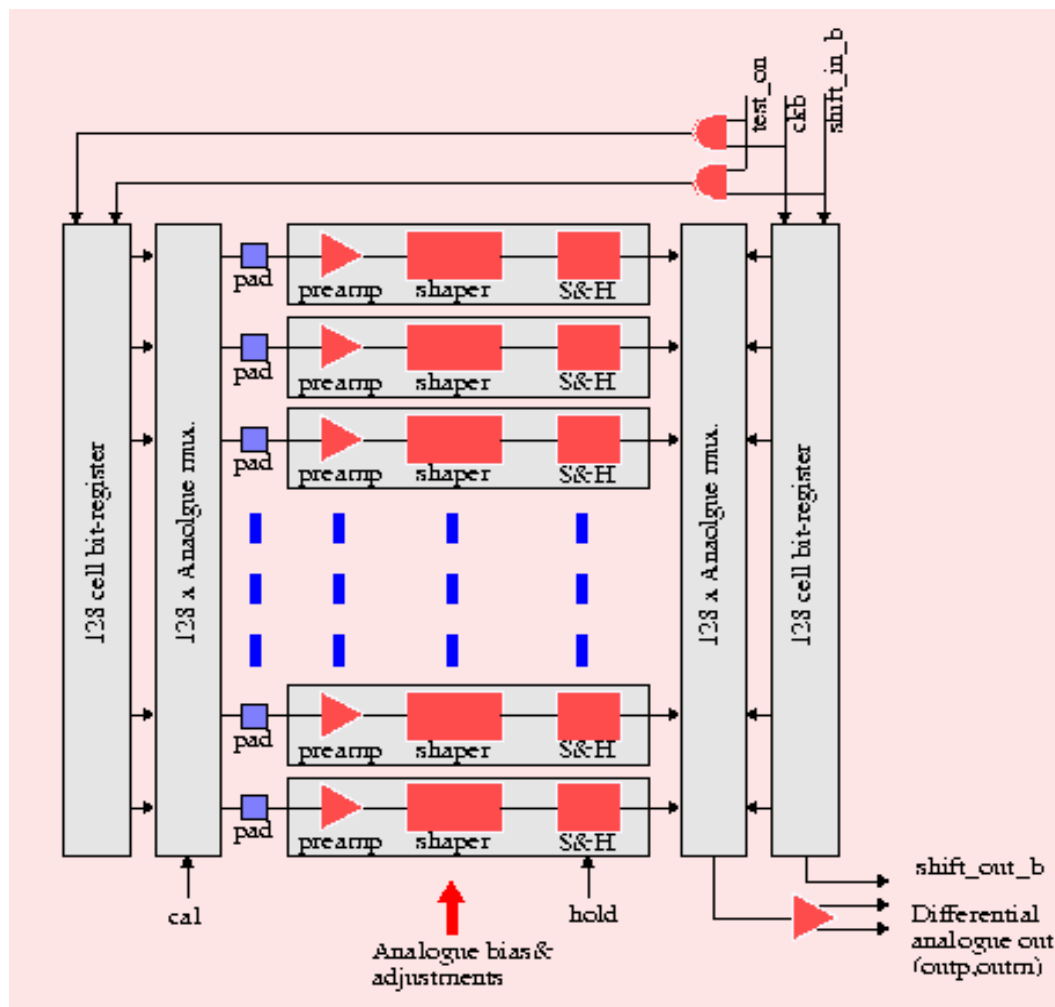
Fig 4. VA1' Architecture

6 Normal mode of operation

The normal mode of operation is that the 128 inputs are connected to a detector from where the charge signal comes. After the physics event, each channel will integrate its eventual signal for 1µs. Usually, after the peak is reached (1µs), an external '**holdb**' signal should be applied to sample the value. Immediately after this a sequential read-out can be performed by activating the output bit-register using '**shift_in_b**' and '**ckb**'. See fig. 5 for an example of the timing in this mode. The logic part of the chip can be reset either by applying the '**dreset**' or, simply by running through a normal read-out once.
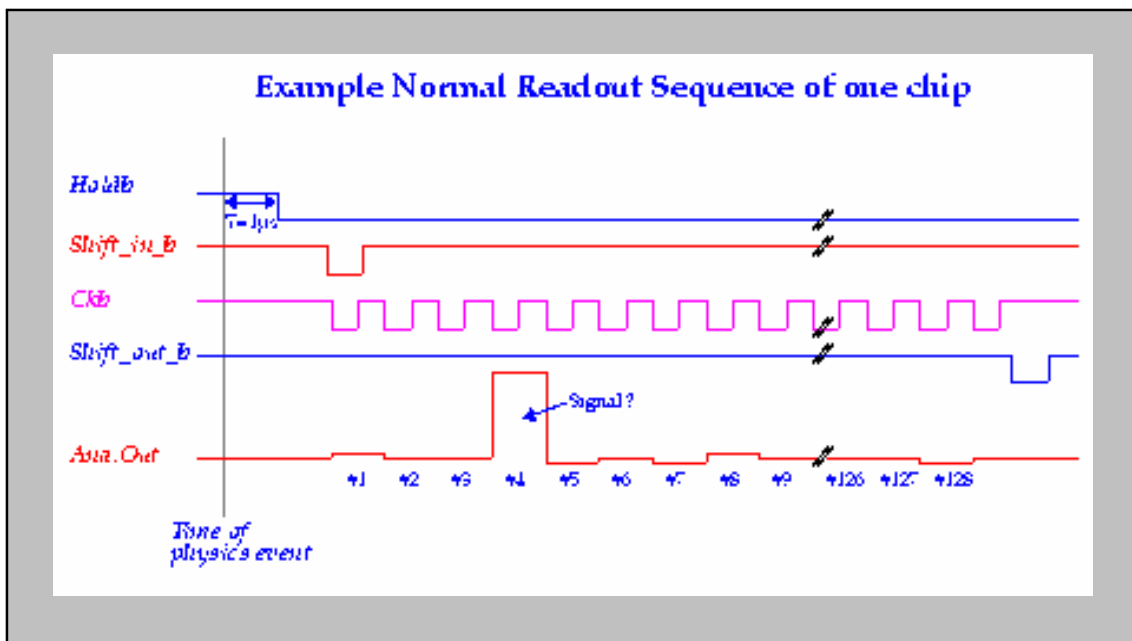
Fig 5. Read-out timing of VA1'

7 Operation in test mode

Each of the inputs of the amplifiers can be accessed via the input pads on the left side, see Fig.4. In test mode, it is not necessary to connect any of these. Instead, the test facility of the chip can be turned on ('**test-on**'). This will enable another mux./bit-register on the input to run exactly in parallel with the output mux./bit-register. This input mux. connects all the inputs to the '**cal**' pad via a switch controlled by the bit-register. Also, in this case, only one connection at a time is possible and this connection will always correspond to the same channel as is connected in the output mux.
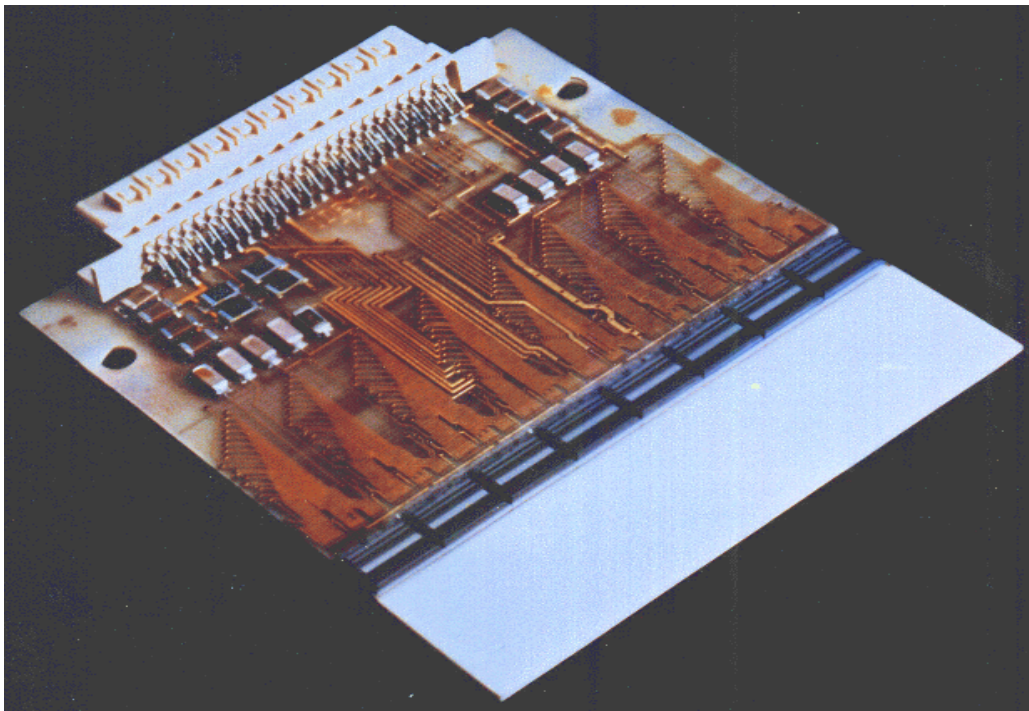

Fig. 6: VA1 circuits on a ceramic-PCB hybrid board

8 Useful hints

Use of 'cal'-input
When the '**cal**'-input is used in test mode an external capacitor (as close as possible to the pad) should be connected in series before the signal enters into the '**cal**' pad. A capacitor value of 1.8 pF is recommended. A voltage step of 2 mV gives hence an input signal charge of 3.6 fC (~ 1 MIP).

Generation of bias-currents/-voltages
Fig. 7. shows a possible approach for generating the necessary bias currents and voltages.

Adjustment of VFP
VFP adjusts the feedback resistor of the pre-amplifier. Lower values result in a higher feedback resistor thus at too negative values the pre-amplifier will stop working.

Termination of outputs
Fig. 8 shows a possible solution for termination of the outputs '**outm**' and '**outp**'.

Decoupling of power and bias lines

It is recommended to decouple the power and bias lines to GND.
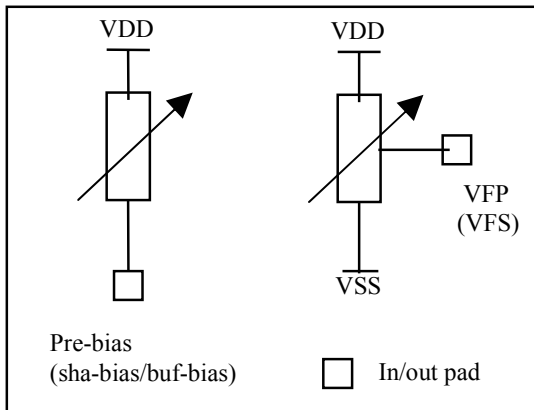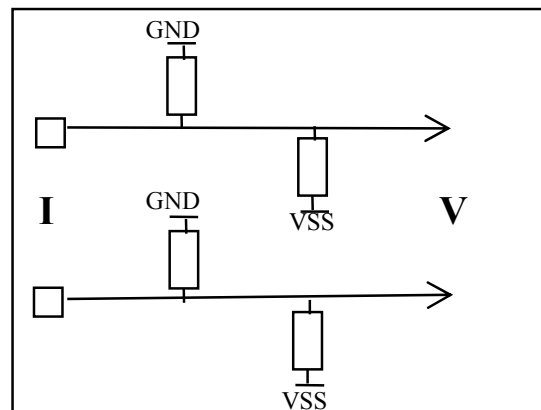
9 Bias current generation

Fig 7. Bias current & Voltage generation   Fig. 8. Analogue-Out termination
(1 kOhm recommended)